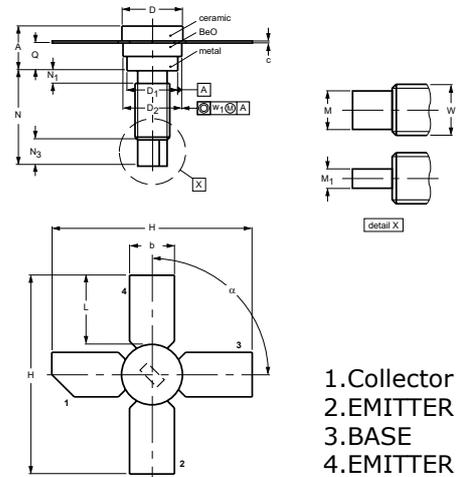


**DESCRIPTION**

Designed for very high output 1.5 V MATV amplifiers up to 860 MHz and 500mW Band V TV transposer stages. Gold metallization and diffused emitter ballast resistors are used to enhanced reliability, ruggedness and linearity.

**FEATURES**

- Specified 20V, 860MHz Characteristics
- $P_o = 0.5W$  @20V, 860MHz
- $G_p = 12.0$  dB (Typ) @28V, 860MHz
- VSWR =  $\infty : 1$
- Omnigold™ Metalization System

**DIMENSIONS**


NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D <sub>1</sub>	D <sub>2</sub>	H	L	M <sub>1</sub>	M	N	N <sub>1</sub> max.	N <sub>3</sub>	Q	W	w <sub>1</sub>	$\alpha$
mm	5.97 4.74	5.85 5.58	0.18 0.14	7.50 7.23	6.48 6.22	7.24 6.93	27.56 25.78	9.91 9.14	3.18 2.66	1.66 1.39	11.82 11.04	1.02	3.86 2.92	3.38 2.74	8-32 UNC	0.381	90°

**MAXIMUM RATINGS**

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Emitter Voltage	$V_{CE0}$	24	V
Collector-Base Voltage	$V_{CB0}$	45	V
Collector-Emitter Voltage	$V_{CES}$	45	V
Collector Current	$I_C$	0.7	A
Emitter-Base Voltage	$V_{EBO}$	3.5	V
Collector Power Dissipation	$P_{DISS}$	8.75	W
Storage Temperature Range	$T_{STG}$	-65 to 150	°C

**ELECTRICAL CHARACTERISTICS**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C=20mA, I_B=0$	24	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CB0}$	$I_C=1mA, I_E=0$	45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=20mA, V_{BE}=0$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=4mA, I_C=0$	3.5	-	-	V
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=28V, I_E=0$	-	-	1.0	mA
Emitter-Base Leakage Current	$I_{EBO}$	$V_{EB}=2.0V, I_E=0$	-	-	0.2	mA
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=100mA$	15	-	120	
Power Gain	$G_p$	$V_{CC}=20V, P_{OUT}=0.5W, f=860MHz$	11.5	12.0	-	dB
Collector Output Capacitance	$C_{ob}$	$V_{CB}=28V, I_E=0, f=1MHz$	-	-	5.5	pF

Note : Above parameters , ratings , limits and conditions are subject to change.